

Rev.A Apr.-2019

N TO-252

N-CHANNEL MOSFET in a TO-252 Plastic Package.

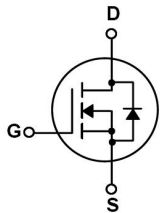
$U_{GS} + r_q$, H , F_{UVV}

Low $R_{DS(on)}$, low gate charge, low C_{rss} , fast switching. Halogen-free Product.

H

DC/DC

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.



PIN 1 G

PIN 2 D

PIN 3 S

PIN 4 D

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	20	V
Drain Current	$I_D(T_c=25^\circ C)$	60	A
	$I_D(T_c=100^\circ C)$	50	A
Drain Current - Pulsed	I_{DM}	210	A
Gate-Source Voltage	V_{GS}	± 12	V
Avalanche Current	I_{AS}	18.3	A
Avalanche energy $L=0.5mH$	E_{AS}	268	mJ
Power Dissipation	$P_D(T_c=25^\circ C)$	100	W
	$P_D(T_c=100^\circ C)$	50	W
Junction and Storage Temperature Range	T_j, T_{stg}	-55 ~ 150	$^\circ C$
Maximum Junction-to-Ambient Steady-State	$R_{\theta JA}$	62	$^\circ C/W$

Parameter	N
	Symbol

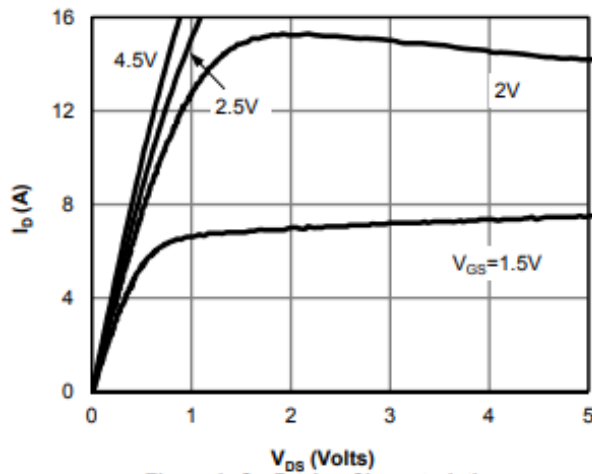


Figure 1: On-Region Characteristics.

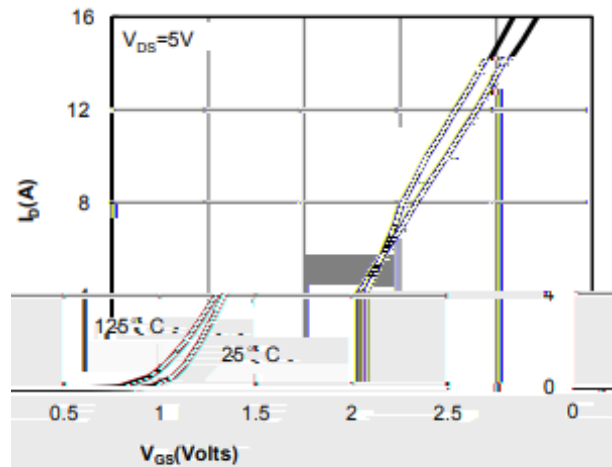


Figure 2: Transfer Characteristics.

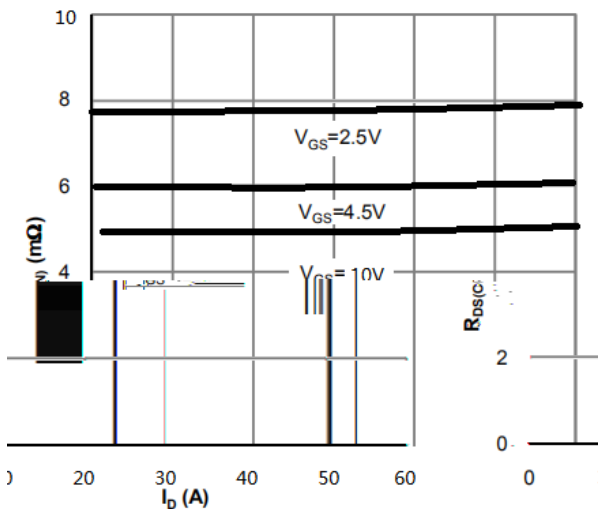


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

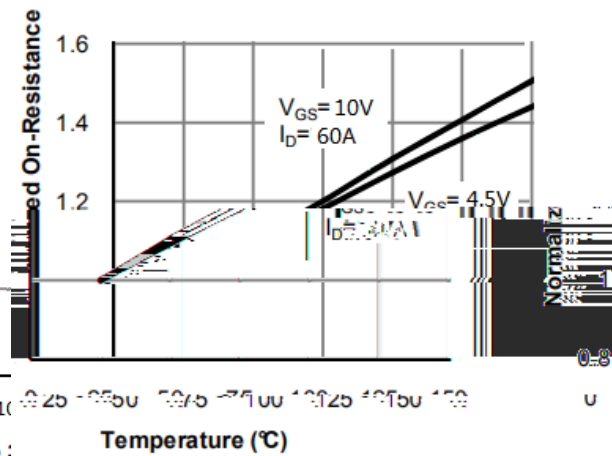


Figure 4: On-Resistance vs. Junction Temperature

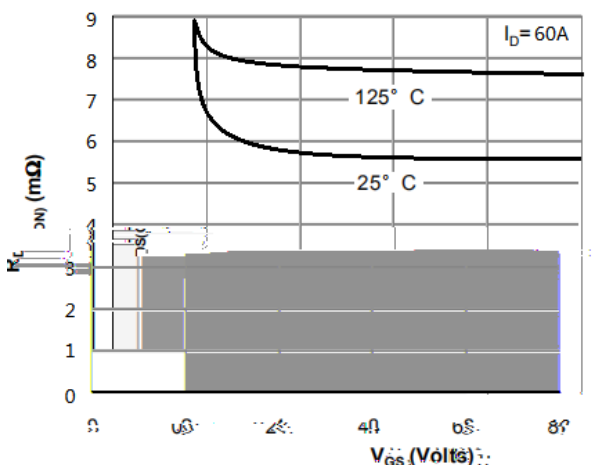


Figure 5: On-Resistance vs. Gate-Source Voltage

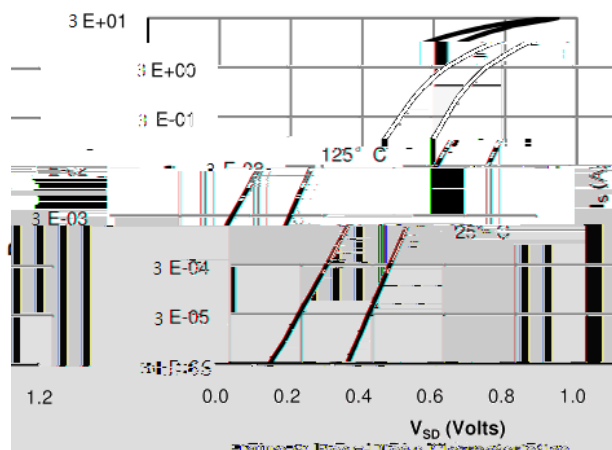


Figure 6: On-Resistance vs. Drain-Source Voltage

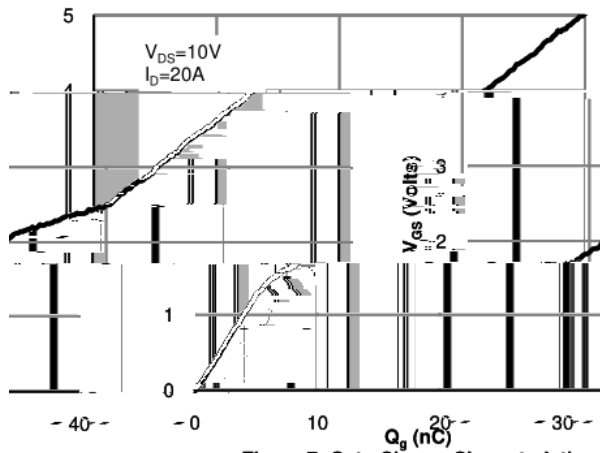


Figure 7: Gate-Charge Characteristics

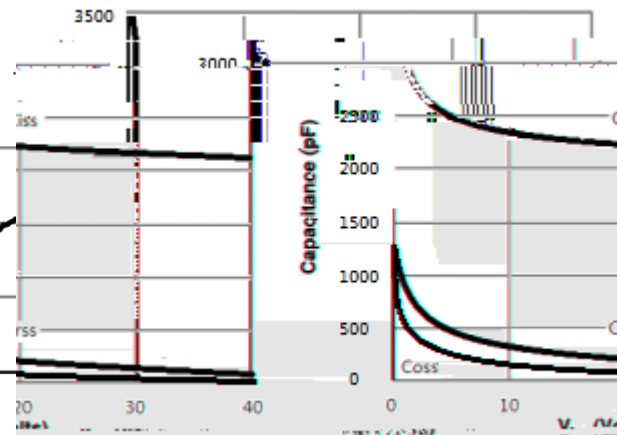
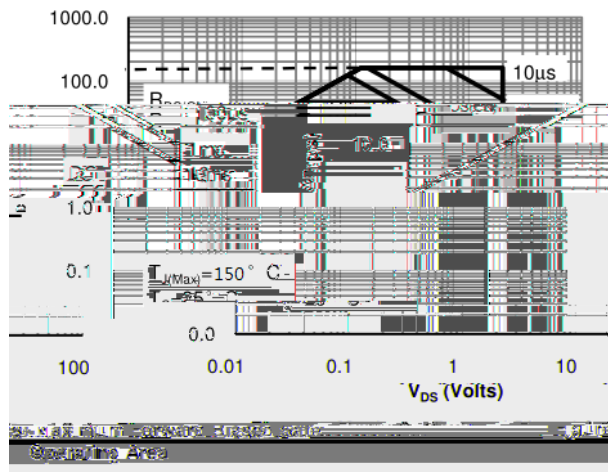
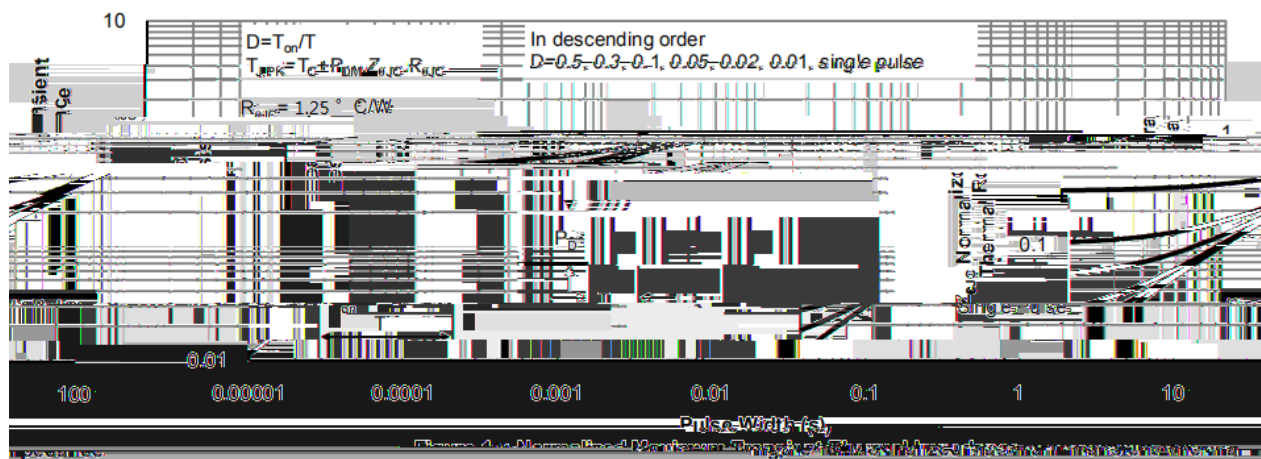
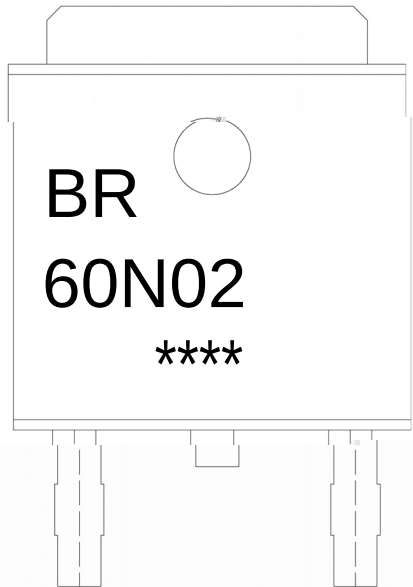


Figure 8: Capacitance Characteristics





BR	N	
60N02	N	
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Note:

BR:	Company Code
60N02:	Product Type Code.
****:	Lot No. Code, code change with Lot No.

